

MICROWAVE POWER GaAs FET

TIM7785-60ULA

MICROWAVE SEMICONDUCTOR TECHNICAL DATA

FEATURES

- ·BROAD BAND INTERNALLY MATCHED FET
- **HIGH POWER**

P1dB= 48.0dBm at 7.7GHz to 8.5GHz

·HIGH GAIN

G1dB= 7.5dB at 7.7GHz to 8.5GHz

·LOW INTERMODURATION DISTORTION

IM3= -30 dBc at Pout= 41.0dBm

Single Carrier Level

·HERMETICALLY SEALED PACKAGE



RF PERFORMANCE SPECIFICATIONS (Ta= 25°C)

CHARACTERISTICS	SYMBOL	CONDITIONS	UNIT	MIN.	TYP.	MAX.
Output Power at 1dB Gain Compression Point	P1dB	VDS= 10V IDSset= 9.5A f = 7.7 to 8.5GHz	dBm	47.0	48.0	_
Power Gain at 1dB Gain Compression Point	G1dB		dB	6.5	7.5	_
Drain Current	IDS1		Α		14.5	16.0
Gain Flatness	ΔG		dB	_	_	±0.8
Power Added Efficiency	ηadd		%		36	
3rd Order Intermodulation Distortion	IM3	Two Tone Test Po= 41.0dBm, Δf= 5MHz (Single Carrier Level)	dBc	-25	-30	_
Drain Current	IDS2		Α	_	_	13.1
Channel Temperature Rise	∆Tch	(VDS X IDS + Pin – P1dB) X Rth(c-c)	°C	_	_	100

Recommended Gate Resistance(Rg): 28 Ω

ELECTRICAL CHARACTERISTICS (Ta= 25°C)

CHARACTERISTICS	SYMBOL	CONDITIONS	UNIT	MIN.	TYP.	MAX.
Transconductance	gm	VDS= 3V IDS= 11.0A	S	_	15.0	_
Pinch-off Voltage	VGSoff	VDS= 3V IDS= 120mA	V	-1.0	-1.8	-2.5
Saturated Drain Current	IDSS	VDS= 3V VGS= 0V	А	_	27	_
Gate-Source Breakdown Voltage	VGSO	IGS= -0.4mA	V	-5		_
Thermal Resistance	Rth(c-c)	Channel to Case	°C/W	_	0.8	1.0

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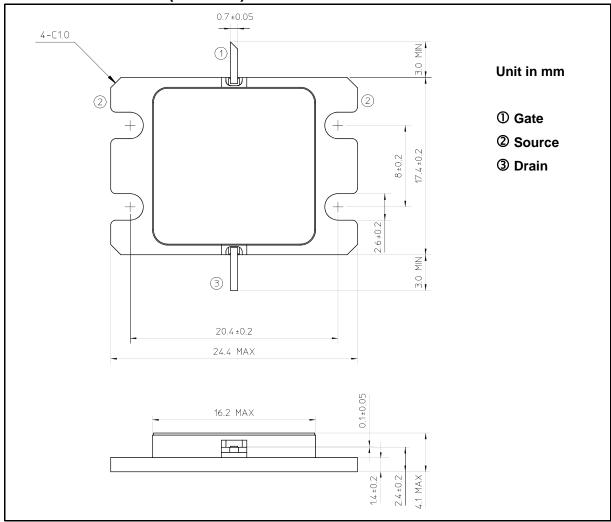


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ABSOLUTE MAXIMUM RATINGS (Ta= 25°C)

CHARACTERISTICS	SYMBOL	UNIT	RATING
Drain-Source Voltage	VDS	V	15
Gate-Source Voltage	VGS	V	-5
Drain Current	IDS	А	20.0
Total Power Dissipation (Tc= 25°C)	PT	W	150
Channel Temperature	Tch	°C	175
Storage	Tstg	°C	-65 to +175

PACKAGE OUTLINE (7-AA09A)



HANDLING PRECAUTIONS FOR PACKAGE MODEL

Soldering iron should be grounded and the operating time should not exceed 10 seconds at 260°C or 3 seconds at 350°C.